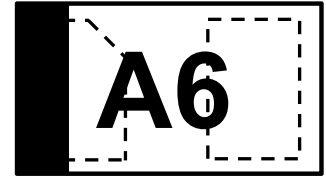


Silicon Epitaxial Planar Switching Diode
DFN1006-2L

Features

- High voltage
- Small package
- Small capacitance

 1.Cathode  2.Anode

Marking Code: A6
Absolute Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$

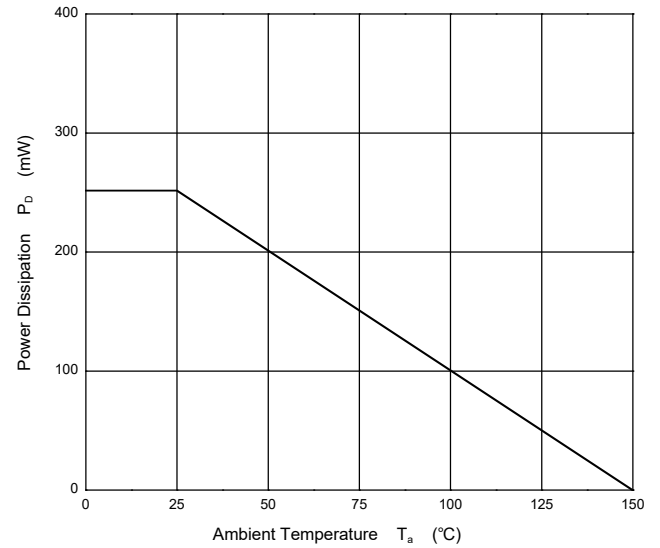
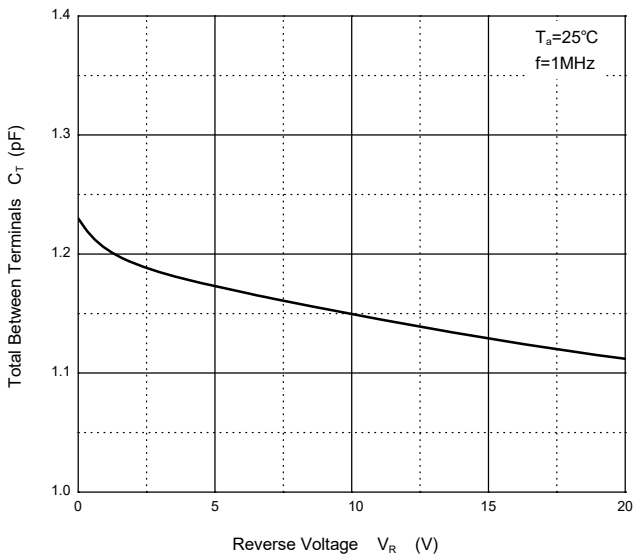
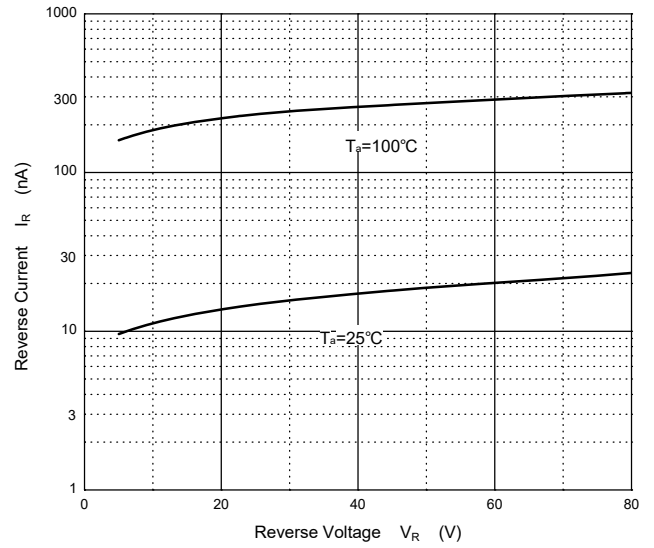
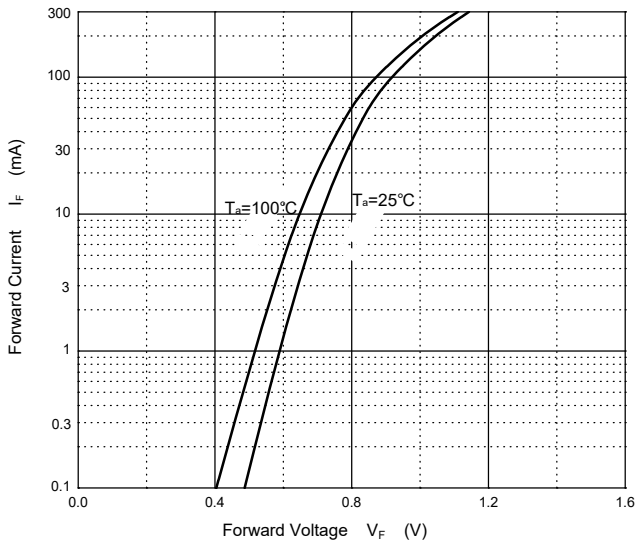
Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
DC Forward Current	I_{FM}	600	mA
Repetitive Peak Forward Current	I_{FRM}	700	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ 1	A
		at $t = 1\text{ }\mu\text{s}$ 4	
Power Dissipation	P_D	250	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Characteristics at $T_A = 25\text{ }^\circ\text{C}$
Silicon Epitaxial Planar Switching Diode

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	--	0.85	V
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$ at $I_R = 5\text{ }\mu\text{A}$	$V_{(BR)R}$	100 75	-- --	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, at $T_A = 150\text{ }^\circ\text{C}$	I_R	-- -- --	25 1 50	nA μA μA
Typical Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_j	--	4	pF
Maximum Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $I_{RR} = 1\text{ mA}$, $R_L = 100\text{ }\Omega$	T_{rr}	--	4	nS

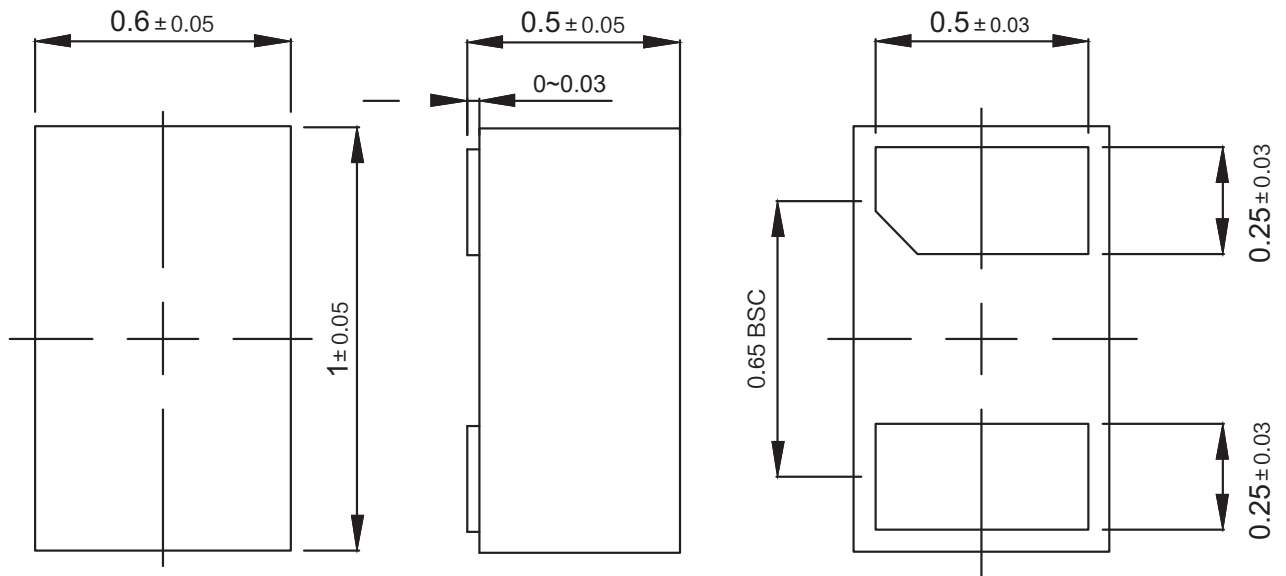
Typical Characteristic Curves

Silicon Epitaxial Planar Switching Diode



Package Outline DFN1006-2

Dimensions in mm



TOP VIEW

SIDE VIEW

BOTTOM VIEW

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
DFN1006-2	Tape/Reel, 7" reel	10000	EIA-481-1